

Page 9, lines 18-19, after each occurrence of "wafer", insert -- 135 --.

Page 10, line 5, change "Fox" to -- For --.

### **In The Claims**

Please cancel claim 13 amend the claims as follows:

1. (Twice Amended) A method for chemical-mechanical polishing a wafer using a CMP apparatus having a polishing table including a polishing pad and a wafer carrier adapted to carry a wafer relative to the center of the polishing table, the method comprising:

using the polishing pad, polishing the wafer at a position relative to the center;

determining that the wafer is being polished in a center-offset manner; and

as a function of the wafer being polished in the center-offset manner, conditioning the pad [as a function of the wafer being polished in the center-offset manner] and positioning the wafer carrier misaligned with respect to the pad.

10. (Amended) A method for chemical-mechanical polishing, according to claim 8, wherein altering the thickness of the pad comprises applying increased pressure to a portion of the pad with [the] a conditioning wheel.

11. (Amended) An arrangement for chemical-mechanical polishing a wafer, the arrangement comprising:

- means for polishing a wafer;
- means for holding a wafer face-down on the means for polishing;
- means for determining whether the wafer is polishing in a center-offset manner; and
- means, responsive to the determination means, for conditioning the [pad] polishing means and positioning the wafer misaligned with respect to the polishing means [responsive to the means for determining whether the wafer is polishing in a center-offset manner].

12. (Amended) An arrangement for chemical-mechanical polishing, the arrangement comprising:

a polishing pad arranged to rotate;  
a wafer carrier arranged to carry a wafer, rotate, and hold the wafer face-down on the polishing pad;

a detection arrangement adapted to detect whether the wafer is polishing in a center-offset manner; and

B3 amended  
a conditioning device adapted [arranged] to condition the pad, [responsive to the detection arrangement] both the conditioning device being arranged, and the wafer carrier being misaligned, relative to the polishing pad as a function of the wafer having been polished in a center-offset manner.

---

B4  
17. (Amended) A method for chemical-mechanical polishing a wafer, using a CMP apparatus having a polishing table including a polishing pad and a wafer carrier adapted to carry a wafer relative to the center of the polishing table, the method comprising:

means for using the polishing pad, polishing the wafer at a position relative to the center;

means for determining that the wafer is being polished in a center-offset manner; [and]

means for compensating for the wafer being polished in a center-offset manner by conditioning the pad as a function of the wafer being polished in the center-offset manner, and positioning the wafer carrier misaligned with respect to the pad.

---

Please add new claims as follows:

---

B5  
18. (New) A method for chemical-mechanical polishing a wafer, according to claim 1, wherein positioning the wafer carrier misaligned with respect to the pad includes positioning the wafer carrier offset relative to a center of the pad.

19. (New) An arrangement for chemical-mechanical polishing a wafer, according to claim 12, wherein the wafer carrier is offset relative to a center of the pad.

---